FMB30NP20E

N And P-Channel Trench Power MOSFET

N-Channel

VDS = 30V,ID =20A

RDS(ON) = 10.7mΩ @ VGS=10V

RDS(ON) = 14.7mΩ @ VGS=4.5V

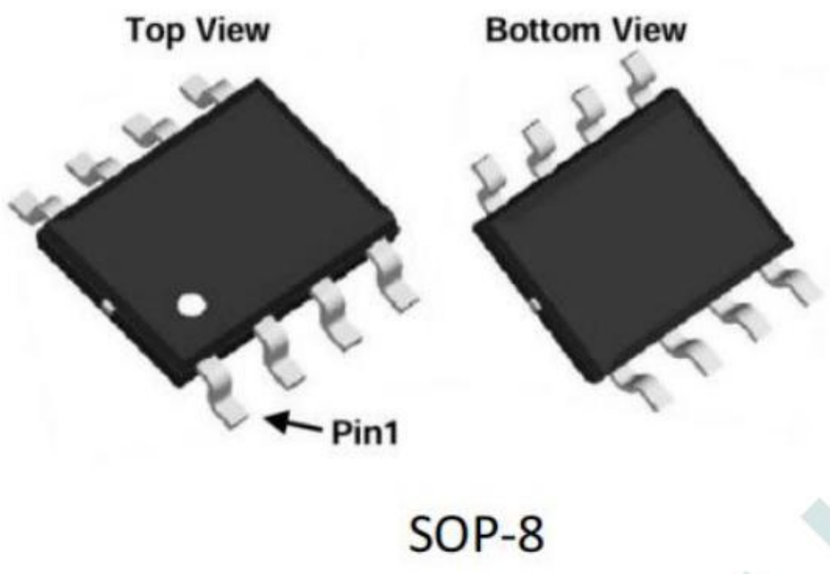
P-Channel

VDS = -30V,ID = -20A

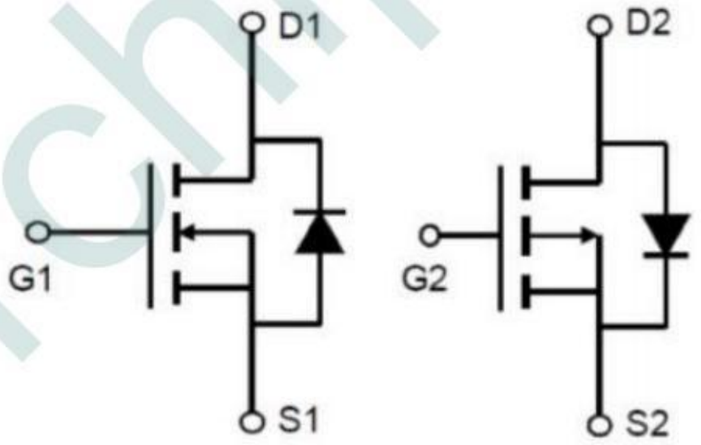
RDS(ON) = 24.3mΩ @ VGS=-10V

RDS(ON) = 34.5mΩ @ VGS=-4.5V

Package



SOP-8



Schematic diagram

Absolute Maximum Ratings (TA=25℃unless otherwise noted)

Symbol	Parameter		Value		Units
			N	P	
V_{DSS}	Drain-Source Voltage		30	-30	V
V_{GSS}	Gate-Source Voltage		±20	±20	V
I_D	Continuous Drain Current	T_C = 25℃	20	-20	A
		T_C = 100℃	16	-12	A
I_{DM}	Pulsed Drain Current note1		79	-57	A
E_{AS},E_{AR}	Single Pulsed Avalanche Energy note2		56	64	mJ
P_D	Power Dissipation	T_C = 25℃	11	13	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case		12	11	℃/W
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	-55 to +150	℃

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